2521/105 2602/106 2601/106 2603/106 ELECTRICAL MEASUREMENT AND ANALOGUE ELECTRONICS June/July 2016 Time: 3 hours





## THE KENYA NATIONAL EXAMINATIONS COUNCIL

# DIPLOMA IN ELECTRICAL AND ELECTRONIC ENGINEERING (INSTRUMENTATION OPTION) (TELECOMMUNICATION OPTION) (POWER OPTION)

## MODULE I

### ELECTRICAL MEASUREMENT AND ANALOGUE ELECTRONICS



#### INSTRUCTIONS TO CANDIDATES

You should have the following for this examination:

Drawing instruments:

Non-programmable electronic calculator;

Mathematical tables.

This paper consists EIGHT questions into TWO sections; A and B.

Answer any THREE questions from section A and any TWO questions from section B in the answer booklet provided.

All questions carry equal marks.

p.J

Maximum marks for each part of a question are as shown.

Candidates should answer the questions in English.

Oscilete,

110x 50

This paper consists of 5 printed pages.

Candidates should check the question paper to ascertain that all the pages are printed as indicated and that no questions are missing.

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## SECTION A: ELECTRICAL MEASUREMENTS

	5			swer any						1 1	7 4	ns	
	(a)	Define	the follo	wing sys	tem of u	nits as	applied	in meas	urements		1 191	V6 () )	
		(i)	absolute	unit:									
		(ii)	derived i		ii.		6.			72		(2 marks)	
	(b)	Derive of unit	the dime	nsions of	the foll								
		(i) (ii)	charge (current (			( G	=2	Faury	Q.	8		(8 marks)	
	(c)	State f	our adva	ntages of	the MK						ents.		
								1-11-		-	T	(4 marks)	
	(d)	Using	the LMT	Í system	of units,	derive	the din	nensional	equation	s for:			
	ě.	(i) (ii)	EMF; magneti	e flux der	nsity. =	Sex il	orsiz.	cont	FIL	Co	laml 6	(6 marks)	
	(a) -	Explai	in the foll	owing ty	pes of m	neasurei	nent er	FOIS:		(1)			
		(i) (ii) (iii) (iv)	instrum gross er residue	mental errors; - & errors	brs; -ce vor dur privis d acute	coverday to to the tens s	to the avacri	fan of the vinderker were const	· In Z Less	()		(8 marks)	ò
	(b)	State t	5	ectors and	their op	eration:	d fregu	encies as	common	ly used f	OF a.c	c. bridges. (6 marks)	
	(c)		in how th wheatston			rs affec	t precis	ioii mea	surement	of media	am re	esistance	
		(1)	tempera	iture effe	cis:								
		(ii)		resistanc									Lov t.
		(iii)		electric o					(riduch			(6 marks)	
3.	(a)	State	three cau	ises of fa	ults on a	printec	l circuit	board.	20			(3 marks)	Low
	(p <sub>j</sub> )	Sulda	ive tools	45								(5 marks)	
	(c)	Expla	ronic equi	points a s	service e history sprvicing	and	should	conside	r when fa	ult findir	ng on	(6 marks)	
	(d)			operation	child	tives an	d three	cost ob	jectives o	f good m	nainte	enance. (6 marks)	
2521/		2602/1		3 seell	7	55250							
2601/ June/J	<b>106</b> uly 2016	2603/1	106		15	2							10.

Describe the term 'reliability' as applied in electrical measurements. to Profom operational merching my viding It is the ability of a Explain the importance of the following in relation to reliability:

- mean time between failures; Time when the muchine will single the work. (i)
- mean time to failure; To Sinva The purpose between in peraul if failure (ii)
- availability. The availability & a (iii)
- (c) Table 1 shows the performance of ten pressure monitors, observed while operating for a period of 1200 hours. Every failed unit is replaced immediately. Determine the:
  - MTBF; (i)
  - (ii) failure rate

(10 marks)

Table 1

Unit Number	Time of Failure (hours)	Failure
1	650	1 ^
2	420	ı
3	· 130 and 725	2
4	585	1
5	630 and 950	2
6	390	Į
7	No failure	0
8	880	1
9	No failure	0
10	220 and 675	2.

State three reasons for the inaccuracies encountered in magnetic measurements, (a)

(3 marks)

(b) Outline six methods of fault location in electronic systems. (6 marks)

- (c) Explain the following wattmeter errors:
  - eddy current errors; (i)
  - stray magnetic field errors. (ii)

(6 marks)

Draw a labelled construction diagram of Hibberts magnetic standard used in magnetic (d) measurements.

(5 marks)

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## SECTION B: ANALOGUE ELECTRONICS

Answer any TWO questions from this section.

1.2

Explain how the following extrinsic semi-conductors are formed. 6. (a)



- (i)
- N-type; -forme by admy perspectant every. P-type. formed by adding townships where. (11)

(4 marks)

- ominer Died State three applications of semi-conductor diodes (b) (i)
  - With aid of voltage-current characteristics, describe the avalanche breakdown (11) (10 marks) in a P-N junction diode.

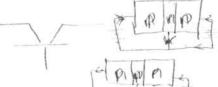


A silicon diode has a forward voltage drop of 1.5V and a forward d.c. current of 150 mA. It has a reverse current of 1.2  $\mu$ A and a reverse voltage of 12 V.  $N_{+} = \sqrt{6} +$ R = V= IR R= Y 15 mm Determine for the diode the:

- forward resistance; 🏠
- (11) reverse resistance. 🗸

(6 marks)

- Draw equivalent two source biaising circuits using the transistor symbol for the following:
  - (1) PNP transistor;
  - (11)NPN transistor.



(4 marks)

- Figure 1 shows an amplifier circuit. (b)
  - Determine the d.c. operating point.
  - (ii) Sketch the d.c. loadline.

a point

(12 marks) NB: neglect V<sub>BE</sub>

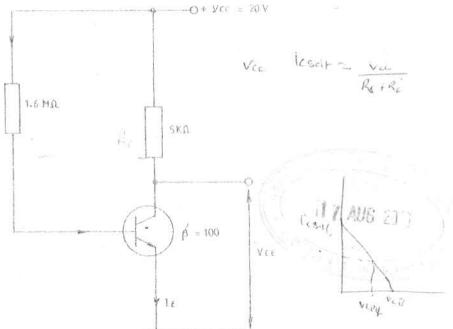


Fig. 1

- (c) State **tw**o advantages and **two** disadvantages of field effect transistors over bipolar junction transistors. (4 marks
- (a) State three advantages of bridge rectifier over bi-phase rectifier.

(3 marks

- (b) (i) With aid of circuit diagram and voltage waveforms, describe the operation of a single phase half wave rectifier feeding a purely resistive load.
  - (ii) Derive the expression for the output d.c. current for the rectifier in b(i).

(11 marks

Position

(c) Figure 2 shows a zener diode stabilizer. Determine the output voltage with no load current. (6 mar

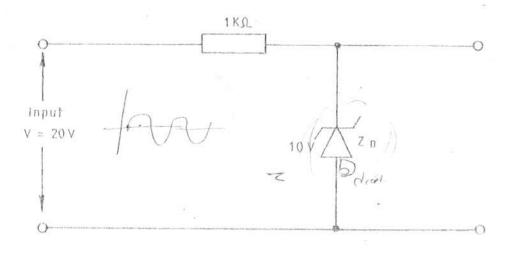


Fig. 2

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